

CoolMOS™ Power Transistor

Features

- Lowest figure-of-merit $R_{ON} \times Q_g$
- Ultra low gate charge
- Extreme dv/dt rated
- High peak current capability
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant

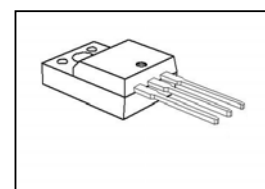
CoolMOS CP is designed for:

- Hard switching SMPS topologies

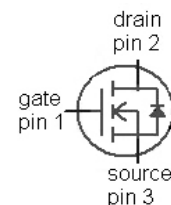
Product Summary

$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max} @ T_j = 25^\circ\text{C}$	0.520	Ω
$Q_{g,typ}$	24	nC

PG-TO220 FP



Type	Package	Marking
IPA60R520CP	PG-TO220 FP	6R520P



Maximum ratings, at $T_j=25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current ²⁾	I_D	$T_C=25^\circ\text{C}$	6.8	A
		$T_C=100^\circ\text{C}$	4.3	
Pulsed drain current ³⁾	$I_{D,pulse}$	$T_C=25^\circ\text{C}$	17	
Avalanche energy, single pulse	E_{AS}	$I_D=2.5\text{ A}, V_{DD}=50\text{ V}$	166	mJ
Avalanche energy, repetitive $t_{AR}^{3),4)}$	E_{AR}	$I_D=2.5\text{ A}, V_{DD}=50\text{ V}$	0.25	
Avalanche current, repetitive $t_{AR}^{3),4)}$	I_{AR}		2.5	A
MOSFET dv/dt ruggedness	dv/dt	$V_{DS}=0\dots480\text{ V}$	50	V/ns
Gate source voltage	V_{GS}	static	± 20	V
		AC ($f>1\text{ Hz}$)	± 30	
Power dissipation	P_{tot}	$T_C=25^\circ\text{C}$	30	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	$^\circ\text{C}$

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous diode forward current ²⁾	I_S	$T_C=25\text{ °C}$	3.8	A
Diode pulse current ³⁾	$I_{S,pulse}$		17	
Reverse diode dv/dt ⁵⁾	dv/dt		15	V/ns

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	4.2	K/W
Thermal resistance, junction - ambient	R_{thJA}	leaded	-	-	62	
Soldering temperature, wavesoldering only allowed at leads	T_{solder}	1.6 mm (0.063 in.) from case for 10 s	-	-	260	°C

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$	600	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=0.34\text{ mA}$	2.5	3	3.5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$	-	-	1	μA
		$V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=150\text{ °C}$	-	10	-	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}$, $I_D=3.8\text{ A}$, $T_j=25\text{ °C}$	-	0.47	0.52	Ω
		$V_{GS}=10\text{ V}$, $I_D=3.8\text{ A}$, $T_j=150\text{ °C}$	-	1.3	-	
Gate resistance	R_G	$f=1\text{ MHz}$, open drain	-	1.3	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$ $f=1\text{ MHz}$	-	630	-	pF
Output capacitance	C_{oss}		-	32	-	
Effective output capacitance, energy related ⁶⁾	$C_{o(er)}$	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 480 V	-	30	-	
Effective output capacitance, time related ⁷⁾	$C_{o(tr)}$		-	77	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=400\text{ V},$ $V_{GS}=10\text{ V}, I_D=3.8\text{ A},$ $R_G=14.7\Omega$	-	17	-	ns
Rise time	t_r		-	12	-	
Turn-off delay time	$t_{d(off)}$		-	74	-	
Fall time	t_f		-	16	-	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD}=400\text{ V}, I_D=3.8\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	3	-	nC
Gate to drain charge	Q_{gd}		-	11	-	
Gate charge total	Q_g		-	24	31	
Gate plateau voltage	$V_{plateau}$		-	4.7	-	V

Reverse Diode

Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=3.8\text{ A},$ $T_j=25\text{ °C}$	-	0.8	1.2	V
Reverse recovery time	t_{rr}	$V_R=400\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	230	-	ns
Reverse recovery charge	Q_{rr}		-	2.5	-	μC
Peak reverse recovery current	I_{rrm}		-	20	-	A

¹⁾ J-STD20 and JESD22

²⁾ Limited only by maximum temperature

³⁾ Pulse width tp limited by $T_{j,max}$

⁴⁾ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

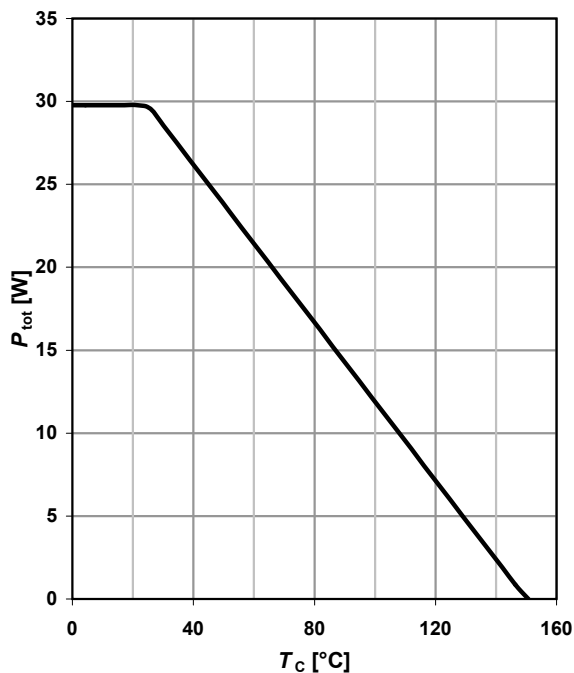
⁵⁾ $I_{SD}=I_D, di/dt \leq 400\text{ A}/\mu\text{s}, V_{DClink}=400\text{ V}, V_{peak} < V_{(BR)DSS}, T_j < T_{j,max}$, identical low side and high side switch

⁶⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⁷⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

1 Power dissipation

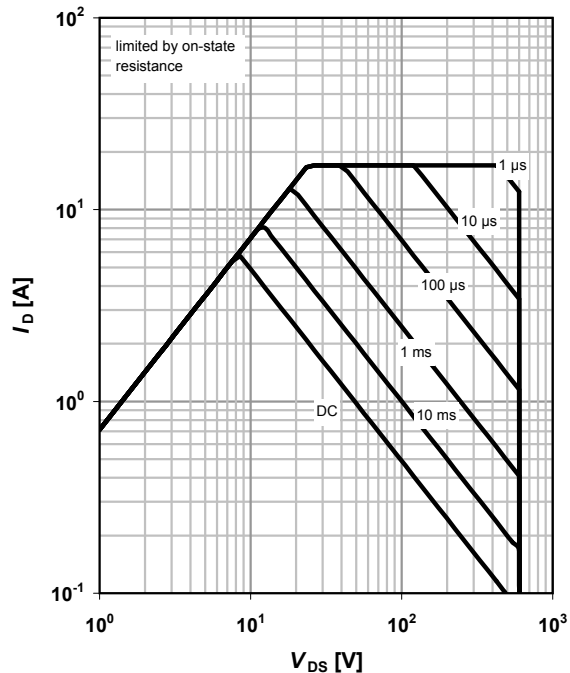
$$P_{\text{tot}} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

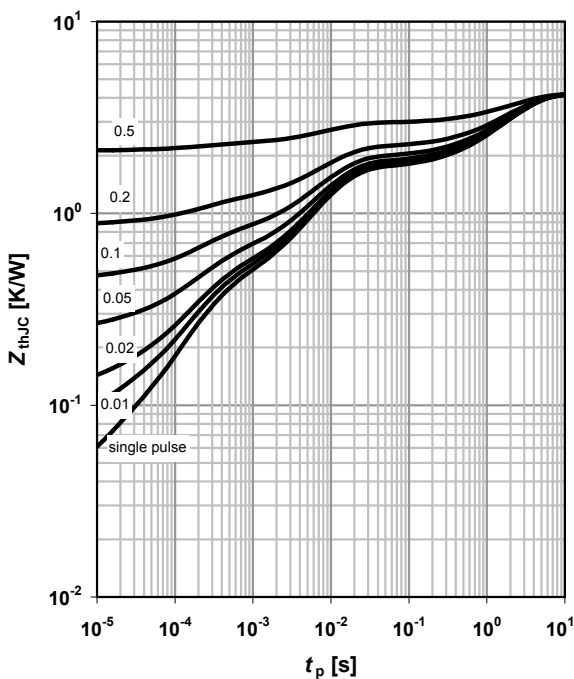
parameter: t_p



3 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

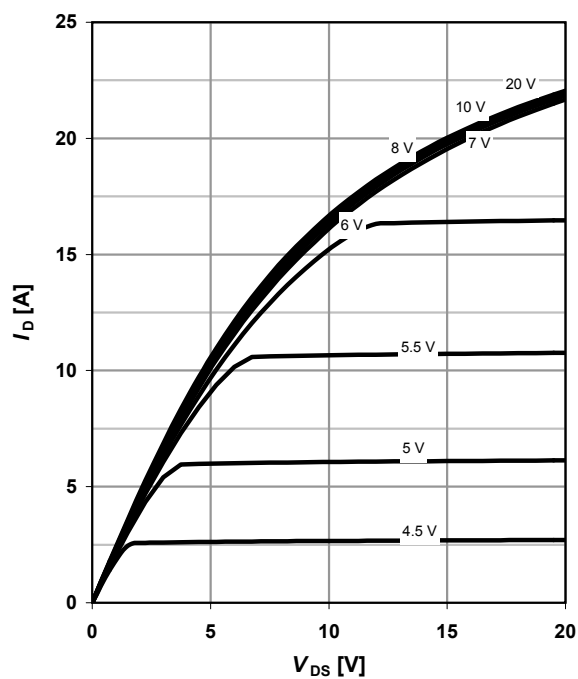
parameter: $D = t_p / T$



4 Typ. output characteristics

$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$$

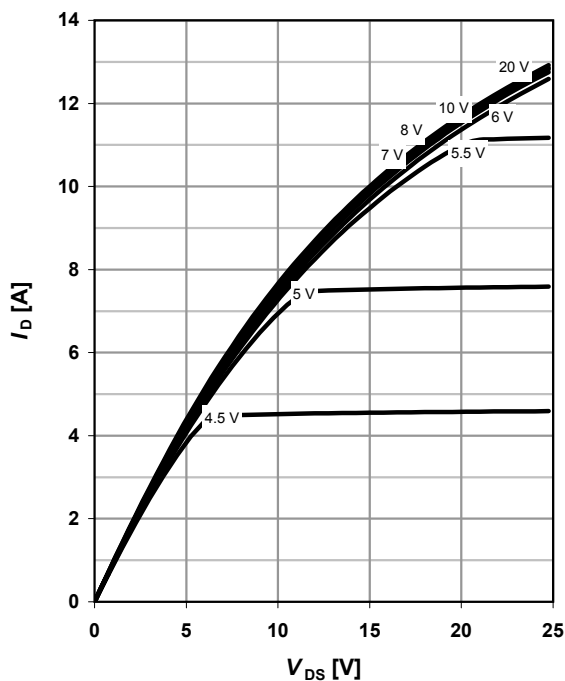
parameter: V_{GS}



5 Typ. output characteristics

$$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$$

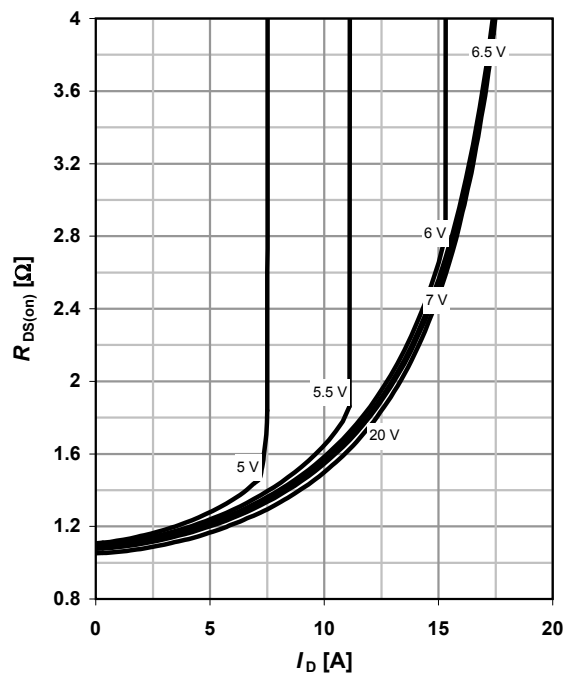
parameter: V_{GS}



6 Typ. drain-source on-state resistance

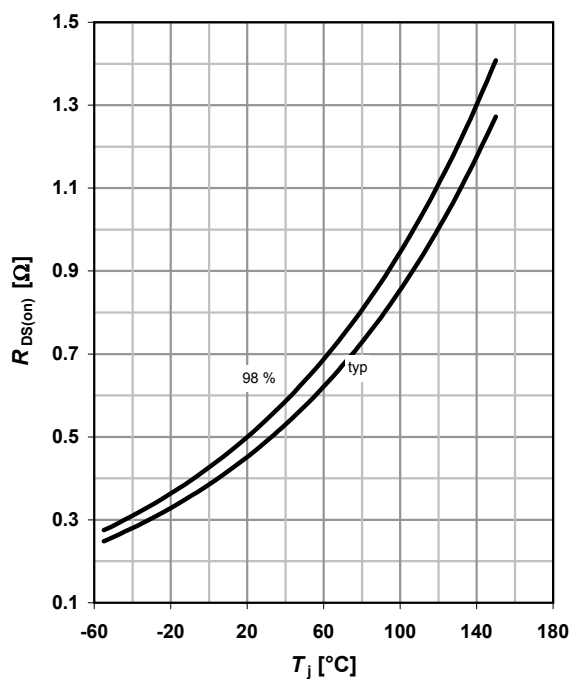
$$R_{DS(on)} = f(I_D); T_j = 150^\circ\text{C}$$

parameter: V_{GS}



7 Drain-source on-state resistance

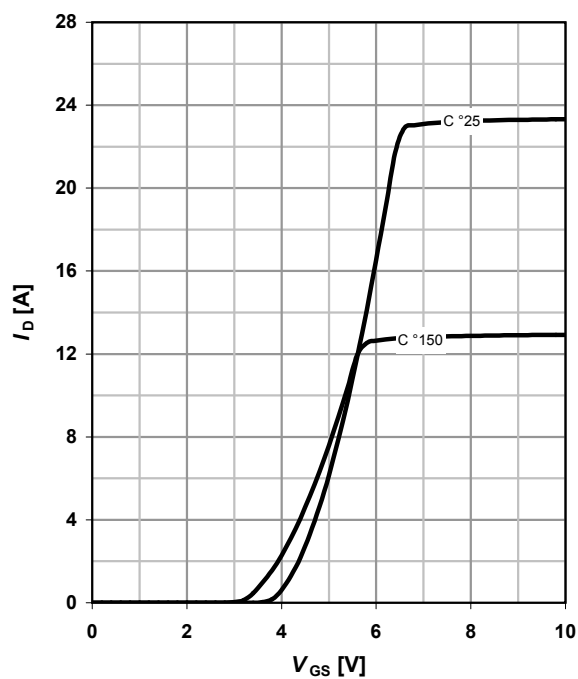
$$R_{DS(on)} = f(T_j); I_D = 3.8\text{ A}; V_{GS} = 10\text{ V}$$



8 Typ. transfer characteristics

$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|/R_{DS(on)\max}$$

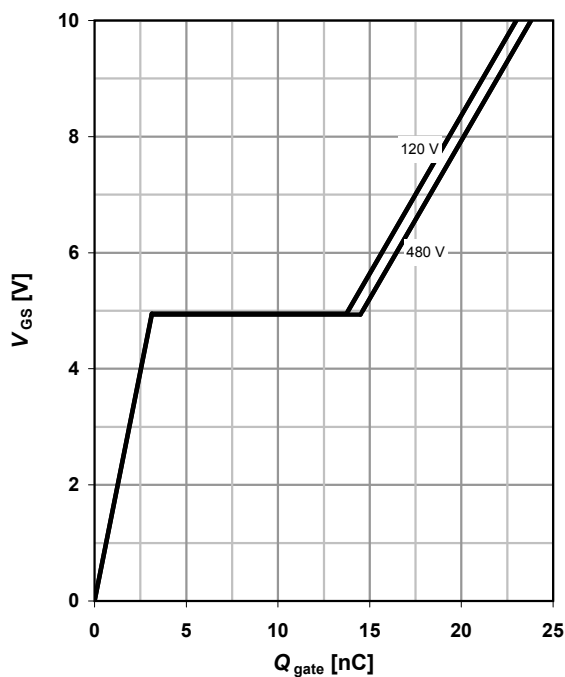
parameter: T_j



9 Typ. gate charge

$$V_{GS}=f(Q_{gate}); I_D=3.8 \text{ A pulsed}$$

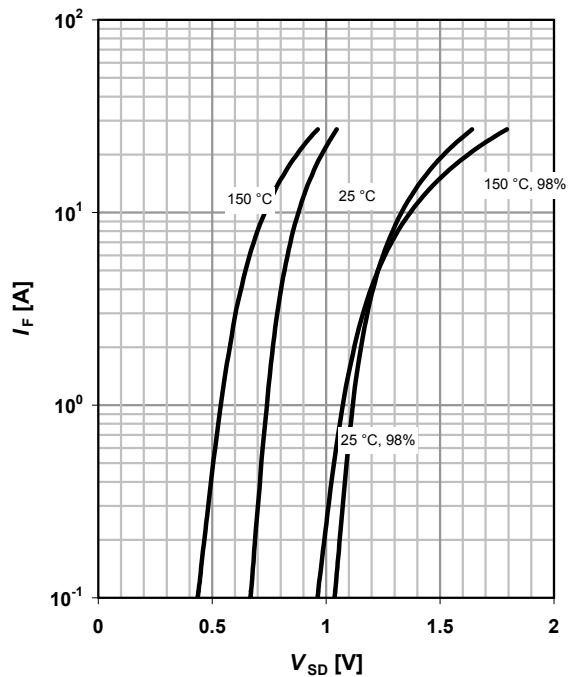
parameter: V_{DD}



10 Forward characteristics of reverse diode

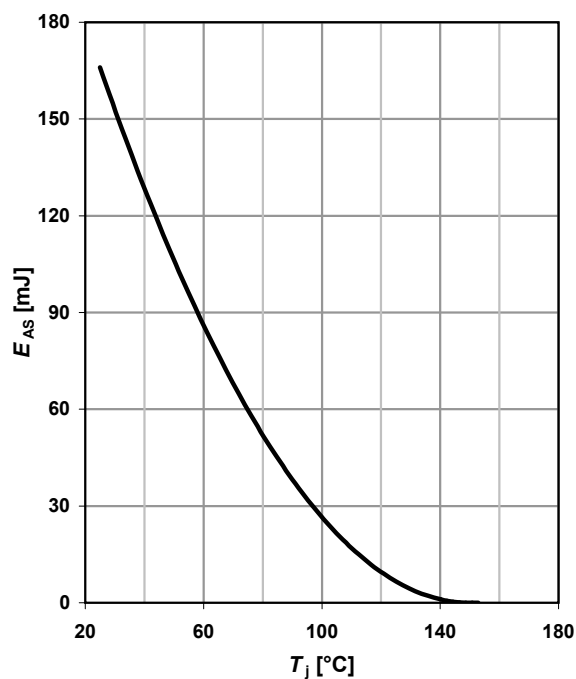
$$I_F=f(V_{SD})$$

parameter: T_j



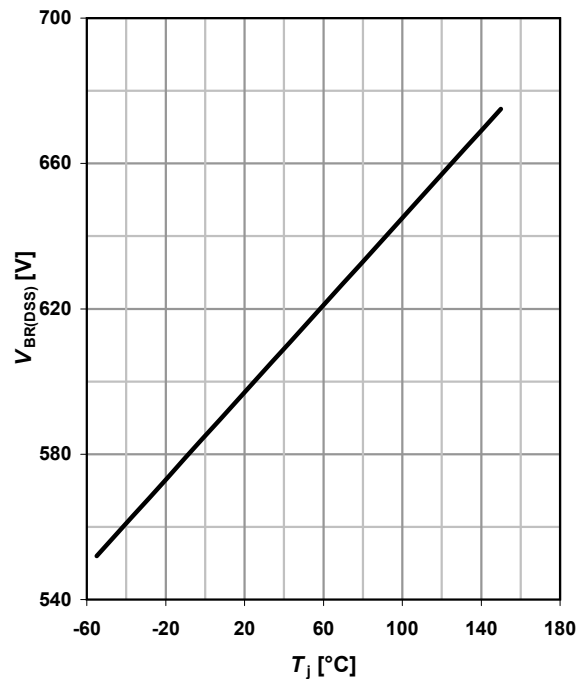
11 Avalanche energy

$$E_{AS}=f(T_j); I_D=2.5 \text{ A}; V_{DD}=50 \text{ V}$$



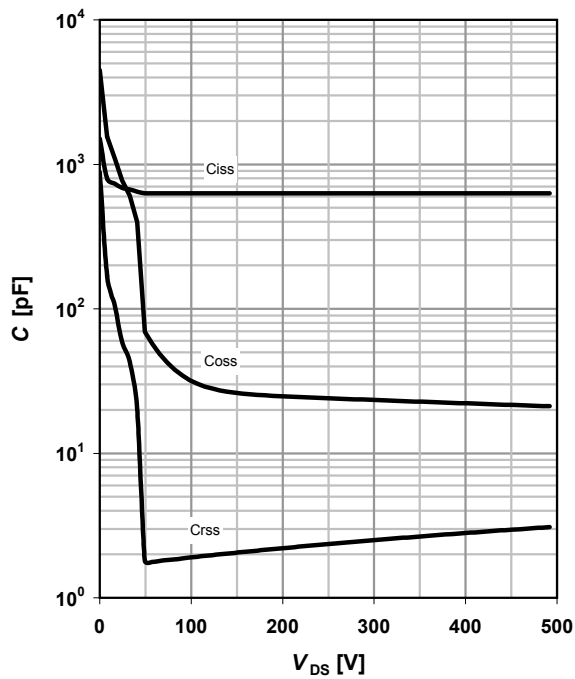
12 Drain-source breakdown voltage

$$V_{BR(DSS)}=f(T_j); I_D=0.25 \text{ mA}$$



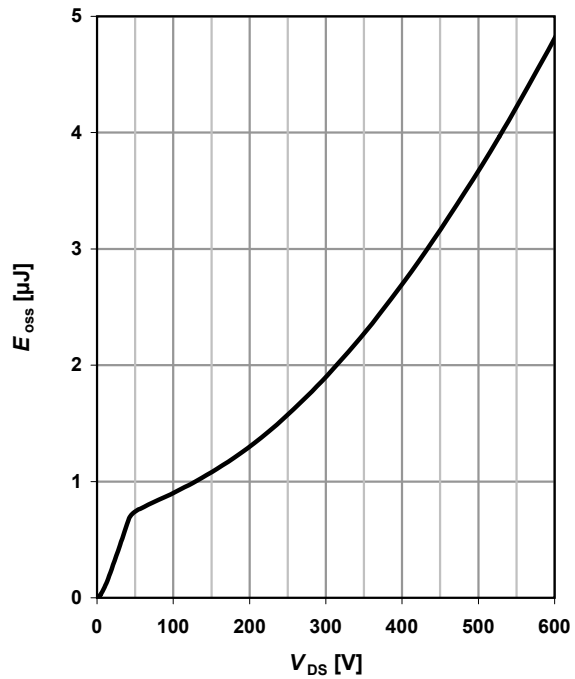
13 Typ. capacitances

$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



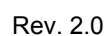
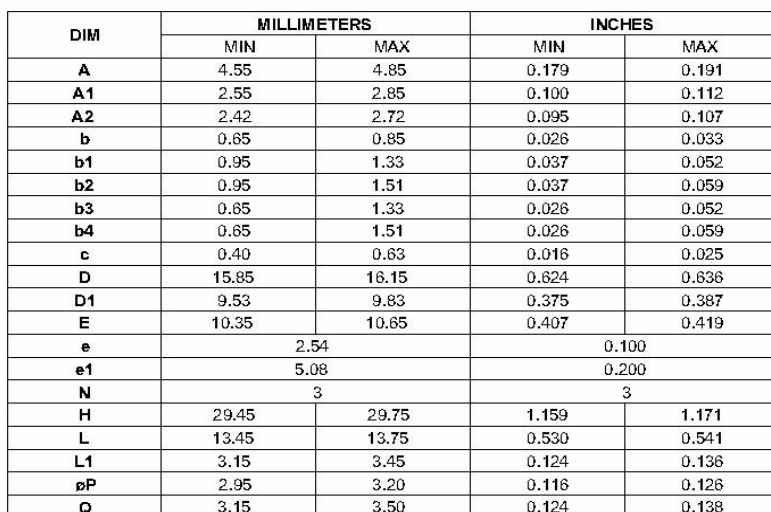
14 Typ. Coss stored energy

$E_{oss} = f(V_{DS})$



Definition of diode switching characteristics


PG-TO220 FP-3: Outlines/Fully isolated packages (2500VAC; 1 minute)



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